

Figures

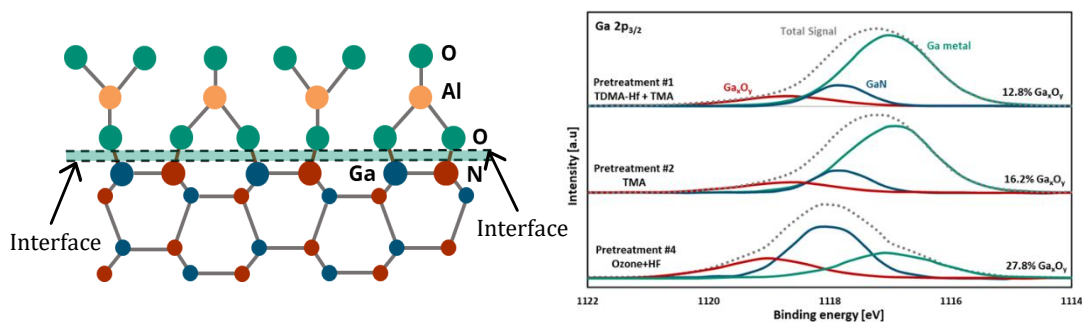


Fig.1: XPS data showing the reduction of Ga_xO_y species following TMA pretreatment prior to thermal Al_2O_3 ALD.

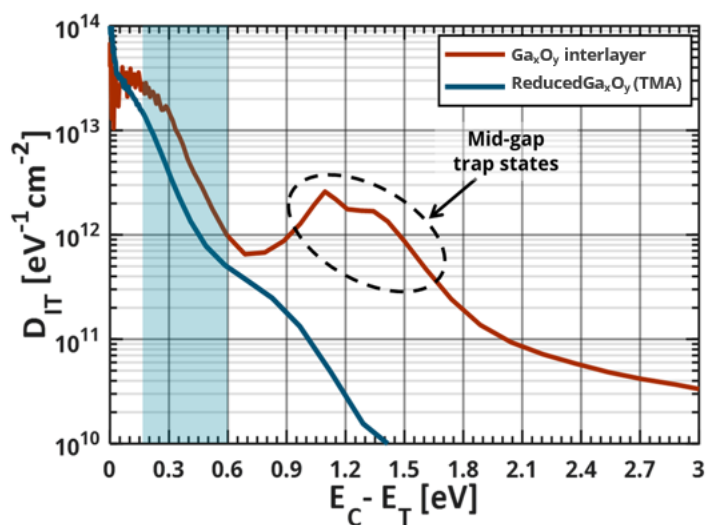


Fig.2: D_{IT} analysis from quasi-static C-V measurements show a decrease of defect densities in GaN MOSCAPs following the reduction of the Ga_xO_y native oxide layer.

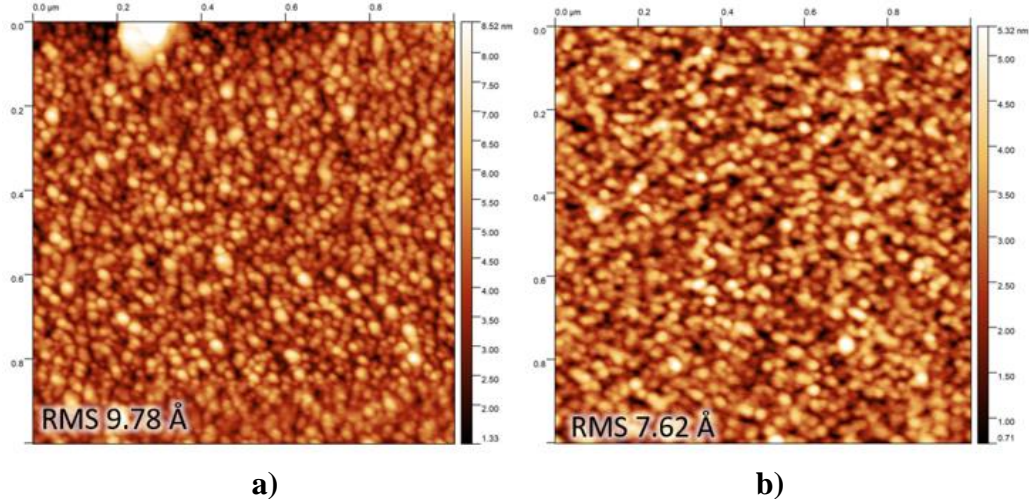


Fig.3: AFM images and RMS surface roughness for (a) GaN coated by Al_2O_3 ALD with no pretreatment and (b) GaN exposed to TMA prior to Al_2O_3 ALD.